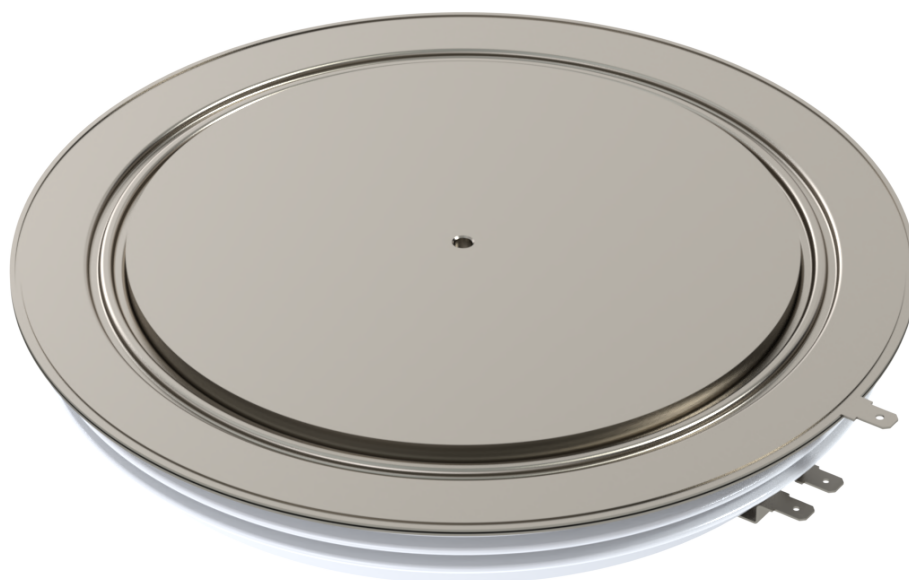


Insulated Gate Bipolar Transistor Type SA45TO1600GG

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Date: August, 2020
Data Sheet Issue: 1



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SA	45	TO	1600	G	G	
-	Voltage Code	Outline Code	Current code	Type code	Special code	Optional code

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Absolute Maximum Ratings

VOLTAGE RATINGS		MAXIMUM LIMITS	UNITS
V_{CES}	Collector-emitter voltage	4500	V
V_{DClink}	Permanent DC voltage for 100 FIT failure rate	2800	V
V_{GES}	Peak gate - emitter voltage	±20	V

OTHER RATINGS		MAXIMUM LIMITS	UNITS
I_C	DC collector current, IGBT	1600	A
I_{CRM}	Repetitive peak collector current, $t_p = 1\text{ms}$, IGBT	3200	A
$I_{F(DC)}$	Continuous DC forward current, Diode	1600	A
I_{FRM}	Repetitive peak forward current, $t_p = 1\text{ms}$, Diode	3200	A
I_{FSM}	Peak non-repetitive surge $t_p = 10\text{ms}$, $V_{RM} = 60\%V_{RRM}$, Diode (note 4)	30	kA
I_{FSM2}	Peak non-repetitive surge $t_p = 10\text{ms}$, $V_{RM} \leq 10\text{V}$, Diode (note 4)	33	kA
P_{MAX}	Maximum power dissipation, IGBT (note 2)	12.8	kW
P_D	Maximum power dissipation, Diode (note 2)	8.13	kW
$(di/dt)_{cr}$	Critical diode di/dt (note 3)	3000	A/ μs
T_j	Operating temperature range	-40 to +125	°C
T_{stg}	Storage temperature range	-40 to +125	°C
note 1)	Unless otherwise indicated $T_j = 125^\circ\text{C}$		
note 2)	$T_{sink} = 25^\circ\text{C}$, doublesidecooled		
note 3)	Maximum commutation loop inductance 200 nH		
note 4)	Half-sinewave, 125°C T_j initial.		

IGBT Characteristics

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNITS
$V_{CE(sat)}$	Collector-emitter saturation voltage	-	2.75	3.2	V
		-	3.50	3.9	V
V_{T0}	Threshold voltage	-	-	1.79	V
r_T	Slope resistance	-	-	1.32	mΩ
$V_{GE(TH)}$	Gate threshold voltage	-	5.1	-	V
I_{CES}	Collector-emitter cut-off current	-	45	70	mA
I_{GES}	Gate leakage current	-	-	±20	μA
C_{ies}	Input capacitance	-	270	-	nF
$t_{d(on)}$	Turn-on delay time	-	2.2	-	μs
$t_r(V)$	Rise time	-	4.4	-	μs
$Q_{g(on)}$	Turn-on gate charge	-	9	-	μC
E_{on}	Turn-on energy	-	12	-	J
$t_{d(off)}$	Turn-off delay time	-	4.8	-	μs
$t_f(I)$	Fall time	-	2.6	-	μs
$Q_{g(off)}$	Turn-off gate charge	-	10	-	μC
E_{off}	Turn-off energy	-	8.7	-	J
I_{SC}	Short circuit current	-	5000	-	A
note 1)	C_{GE} is additional gate-emitter capacitance added to output of gate drive				
note 2)	Figures 4 to 10 are obtained using integral Diode aus freewheeling diode				

Diode Characteristics

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNITS
V_{FM}	Forward voltage	-	3.3	3.6	V
		-	3.45	3.8	V
V_{T0}	Threshold Voltage	-	-	2.14	V
r_T	Slope resistance	-	-	1.04	mΩ
I_{RRM}	Peak reverse recovery current	-	1270	-	A
Q_{rr}	Recovered charge	-	1960	-	μC
t_{rr}	Reverse recovery time, 50% Chord	-	1.75	-	μs
E_r	Reverse recovery energy	-	2.03	-	J

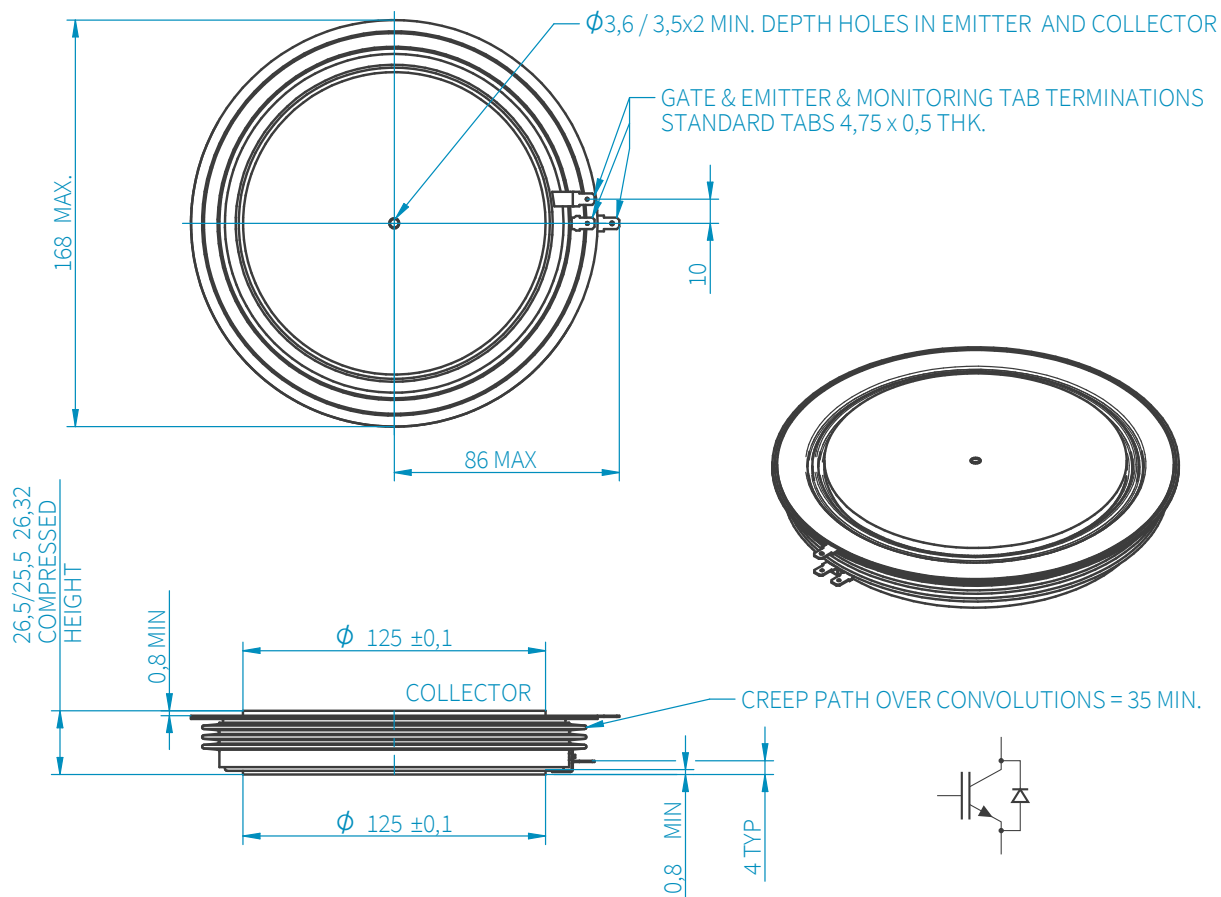
Thermal Characteristics

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNITS
R _{thJK}	Double side cooled	-	-	7.8	K/kW
	Thermal resistance, junction to sink, IGBT Collector side cooled	-	-	12.8	K/kW
	Emitter side cooled	-	-	20.3	K/kW
R _{thJK}	Double side cooled	-	-	12.3	K/kW
	Thermal resistance, junction to sink, Diode Cathode side cooled	-	-	19.5	K/kW
	Anode side cooled	-	-	35.7	K/kW
F	Mounting force	Note 2	50	-	70 kN
W _t	Weight	-	2000	-	g
note 1)	Unless otherwise indicated T _j = 125°C				
note 2)	Consult application note for detailed mounting requirements				

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